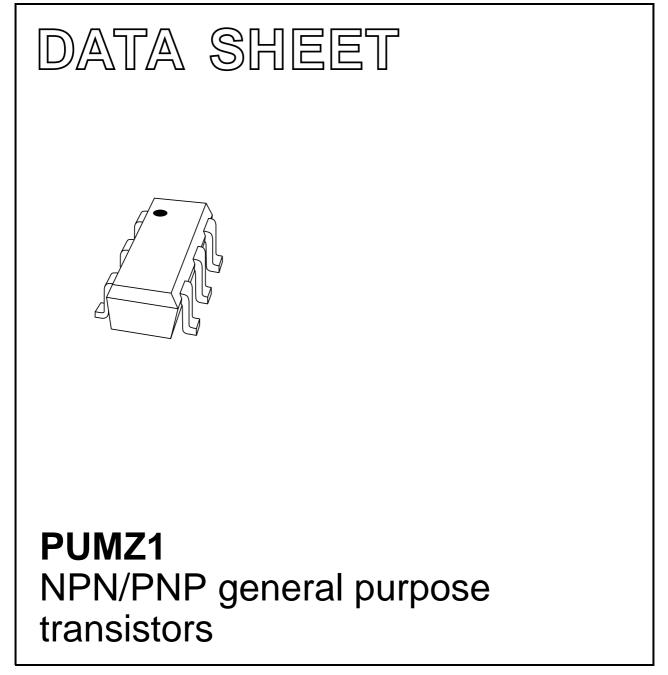
## DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 2002 May 6 2004 Oct 15



#### FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 40 V)
- Reduces number of components and boardspace.

#### APPLICATIONS

• General purpose switching and amplification.

#### DESCRIPTION

Two independently operating NPN/PNP transistors in an SC-88; SOT363 plastic package.

#### MARKING

TYPE NUMBER	MARKING CODE <sup>(1)</sup>
PUMZ1	F*Z

#### Note

- 1. \* = -: Made in Hong Kong.
  - \* = t: Made in Malaysia.
  - \* = W: Made in China.

#### **ORDERING INFORMATION**

TYPE NUMBER	PACKAGE		
ITPE NUMBER	NAME	NAME DESCRIPTION VERSION	
PUMZ1	_	plastic surface mounted package; 6 leads	SOT363

2

### PINNING

PIN		DESCRIPTION
1, 4	emitter	TR1; TR2
2, 5	base	TR1; TR2
3, 6	collector	TR2; TR1

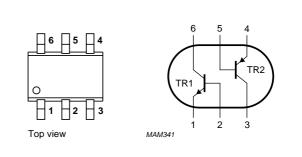


Fig.1 Simplified outline (SC-88) and symbol.

PUMZ1

### PUMZ1

#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT	
Per transis	Per transistor; for the PNP transistor with negative polarity					
V <sub>CBO</sub>	collector-base voltage	open emitter	_	50	V	
V <sub>CEO</sub>	collector-emitter voltage	open base	_	40	V	
V <sub>EBO</sub>	emitter-base voltage	open collector	_	5	V	
I <sub>C</sub>	collector current (DC)		-	100	mA	
I <sub>CM</sub>	peak collector current		_	200	mA	
I <sub>BM</sub>	peak base current		_	200	mA	
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	-	200	mW	
T <sub>stg</sub>	storage temperature		-65	+150	°C	
Tj	junction temperature		-	150	°C	
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C	
Per device	9	·				
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	_	300	mW	

#### Note

1. Device mounted on an FR4 printed-circuit board.

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per device				
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	note 1	416	K/W

#### Note

1. Device mounted on an FR4 printed-circuit board.

### PUMZ1

#### CHARACTERISTICS

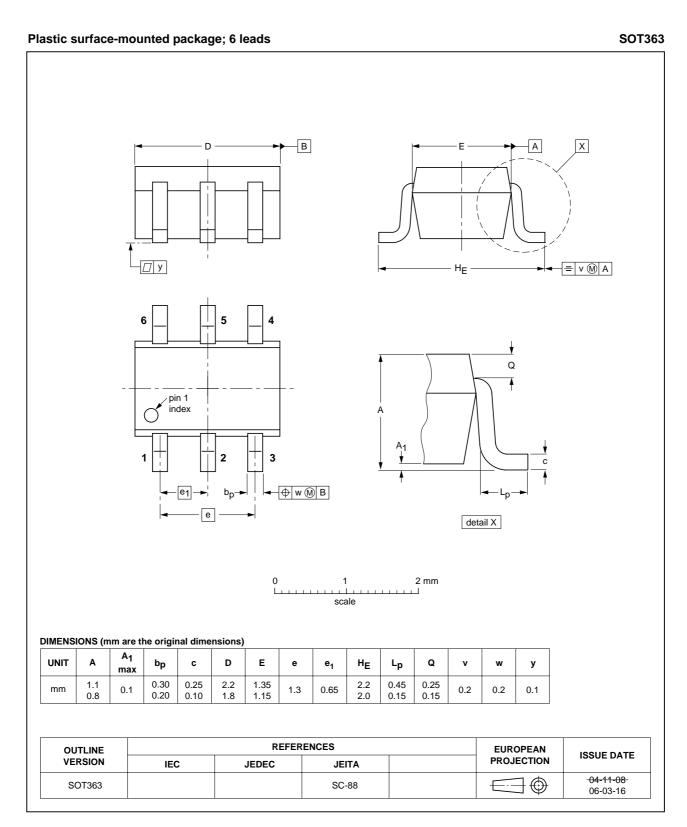
 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT		
Per transist	Per transistor; for the PNP transistor with negative polarity						
I <sub>CBO</sub>	collector-base cut-off current	I <sub>E</sub> = 0 A; V <sub>CB</sub> = 30 V	_	100	nA		
		$I_E = 0 \text{ A}; V_{CB} = 30 \text{ V}; T_j = 150 \text{ °C}$	-	10	μA		
I <sub>EBO</sub>	emitter-base cut-off current	$I_{C} = 0 \text{ A}; V_{EB} = 4 \text{ V}$	_	100	nA		
h <sub>FE</sub>	DC current gain	I <sub>C</sub> = 1 mA; V <sub>CE</sub> = 6 V	120	-			
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{\rm C} = 50 \text{ mA}; I_{\rm B} = 5 \text{ mA}; \text{ note } 1$	-	200	mV		
Cc	collector capacitance	I <sub>E</sub> = i <sub>e</sub> = 0 A; V <sub>CB</sub> = 12 V; f = 1 MHz					
	TR1		_	1.5	pF		
	TR2		_	2.2	pF		
f <sub>T</sub>	transition frequency	$I_{C} = 2 \text{ mA}; V_{CE} = 12 \text{ V}; \text{ f} = 100 \text{ MHz}$	100	_	MHz		

Note

1. Pulse test:  $t_p \leq 300~\mu s;~\delta \leq 0.02.$ 

#### PACKAGE OUTLINE



PUMZ1

PUMZ1

#### DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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## **NXP Semiconductors**

#### **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

#### **Contact information**

For additional information please visit: http://www.nxp.com For sales offices addresses send e-mail to: salesaddresses@nxp.com

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